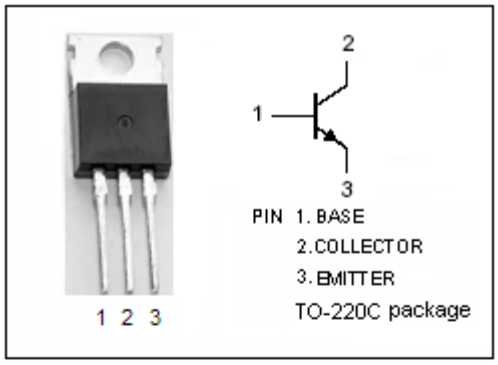
isc Silicon NPN Power Transistor 2SD960

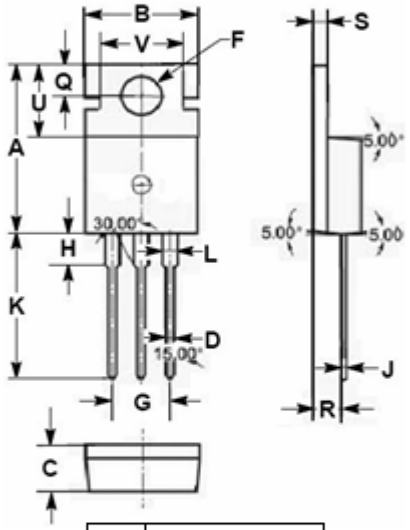


DESCRIPTION

- Collector-Emitter Breakdown Voltage-
  : $V_{(BR)CEO}$= 80V(Min)
- Low Collector-Emitter Saturation Voltage-
  : $V_{CE(sat)}$= 0.5V(Max) @I_C= 3A
- Complement to Type 2SB868

APPLICATIONS

- Designed for power switching applications.



DIM	mm MIN	mm MAX
A	15.70	15.90
B	9.90	10.10
C	4.20	4.40
D	0.70	0.90
F	3.40	3.60
G	4.98	5.18
H	2.70	2.90
J	0.44	0.46
K	13.20	13.40
L	1.10	1.30
Q	2.70	2.90
R	2.50	2.70
S	1.29	1.31
U	6.45	6.65
V	8.66	8.86

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	130	V
V_{CEO}	Collector-Emitter Voltage	80	V
V_{EBO}	Emitter-Base Voltage	7	V
I_C	Collector Current-Continuous	4	A
I_{CM}	Collector Current-Peak	8	A
P_C	Collector Power Dissipation @ T_C=25℃	35	W
T_J	Junction Temperature	150	℃
T_{stg}	Storage Temperature Range	-55~150	℃

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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	I_C= 10mA; I_B= 0	80			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C= 3.0A; I_B= 0.15A			0.5	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	I_C= 3.0A; I_B= 0.15A			1.5	V
I_{CBO}	Collector Cutoff Current	V_{CB}= 100V; I_E= 0			10	μA
I_{EBO}	Emitter Cutoff Current	V_{EB}= 5V; I_C= 0			50	μA
h_{FE-1}	DC Current Gain	I_C= 0.1A; V_{CE}= 2V	45			
h_{FE-2}	DC Current Gain	I_C= 1A; V_{CE}= 2V	60		260	
f_T	Current-Gain—Bandwidth Product	I_C= 0.5A; V_{CE}= 10V		30		MHz

Switching times

t_{on}	Turn-on Time	I_C= 1A, I_{B1}= -I_{B2}= 0.1A		0.5		μs
t_{stg}	Storage Time			2.5		μs
t_f	Fall Time			0.15		μs

◆ **h_{FE-2} Classifications**

R	Q	P
60-120	90-180	130-260